

In the Specification

At page 50 and 51, kindly replace the paragraph bridging pages 50 and 51 with the following:

Referring now to FIG. 29, a vertical cavity surface emitting laser or VCSEL 146 in accordance with the present invention is shown. VCSEL 146 is shown as a GaAlAs device structured and configured for output at approximately 821.9 nm, and it should be readily understood that the layer thicknesses and semiconductor materials used for VCSEL 146 may vary as required for different applications. Thus, VCSEL 146 may be fabricated from various semiconductor materials, including, for example, GaAs, InGaAs, InGaAsP and InP materials, and can be structured and configured to provide various output wavelengths. The thicknesses of various layer components of VCSEL 146 as shown in FIG. 29 are exaggerated for clarity, and the particular layer thicknesses shown are merely illustrative and are not necessarily to scale.

In the Claims

Kindly amend claims 1, 9, 17, 19, and 20 as follows:

a¹

1. A near field optical apparatus comprising:
a conductive layer defining an aperture therein, said aperture having a perimeter;
said conductive layer having at least one protrusion extending into said aperture at said perimeter, wherein said protrusion into said aperture is configured to produce a transmission mode with very high throughput.